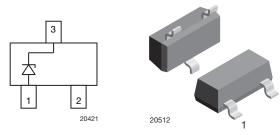
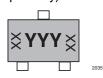


Single-Line ESD Protection in SOT-23



MARKING (example only)



YYY = type code (see table below) XX = date code

DESIGN SUPPORT TOOLS

Models



FEATURES

- Single-line ESD protection device
- ESD immunity acc. IEC 61000-4-2
 - ± 30 kV contact discharge
 - ± 30 kV air discharge
- ESD capability according to AEC-Q101: human body model: class H3B: > 8 kV
- Space saving SOT-23 package
- e3 Sn
- AEC-Q101 qualified available
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912





HALOGEN FREE

GREEN (5-2008)

ORDERING INFORMATION							
	ENVIR	ONMENTAL AN	ID QUALITY CO	ODE	PACKAG	ING CODE	
PART NUMBER (EXAMPLE)	AEC-Q101	RoHS-COM LEAD (P		TIN PLATED	3K PER 7" REEL (8 mm TAPE),	10K PER 13" REEL (8 mm TAPE),	ORDERING CODE (EXAMPLE)
(EXAMPLE)	QUALIFIED	STANDARD	GREEN	PLATED	15K/BOX = MOQ	10K/BOX = MOQ	
GSOT05-		E		3	-08		GSOT05-E3-08
GSOT05-			G	3	-08		GSOT05-G3-08
GSOT05-	Н	E		3	-08		GSOT05-HE3-08
GSOT05-	Н		G	3	-08		GSOT05-HG3-08
GSOT05-		E		3		-18	GSOT05-E3-18
GSOT05-			G	3		-18	GSOT05-G3-18
GSOT05-	Н	E		3		-18	GSOT05-HE3-18
GSOT05-	Н		G	3		-18	GSOT05-HG3-18

PACKA	GE DATA	1					
DEVICE NAME	PACKAGE NAME	TYPE CODE	ENVIRONMENTAL STATUS	WEIGHT	MOLDING COMPOUND FLAMMABILITY RATING	MOISTURE SENSITIVITY LEVEL	SOLDERING CONDITIONS
GSOT03	SOT-23	03	Standard	8.8 mg	UL 94 V-0	MSL level 1	Peak temperature max. 260 °C
	00. 20	03G	Green	8.1 mg	020.00	(according J-STD-020)	r san tomporataro masti 200 °C
GSOT04	SOT-23	04	Standard	8.8 mg	UL 94 V-0	MSL level 1	Peak temperature max. 260 °C
400104	001 20	04G	Green	8.1 mg	020470	(according J-STD-020)	T can temperature max. 200 °C
GSOT05	SOT-23	05	Standard	8.8 mg	UL 94 V-0	MSL level 1	Peak temperature max. 260 °C
G00103	001 20	05G	Green	8.1 mg	OL 34 V 0	(according J-STD-020)	T cak temperature max. 200 G
GSOT08	SOT-23	08	Standard	8.8 mg	UL 94 V-0	MSL level 1	Peak temperature max. 260 °C
G30100	301-23	08G	Green	8.1 mg	OL 94 V-0	(according J-STD-020)	Fear temperature max. 200 C
GSOT12	SOT-23	12	Standard	8.8 mg	UL 94 V-0	MSL level 1	Peak temperature max. 260 °C
G30112	301-23	12G	Green	8.1 mg	OL 94 V-0	(according J-STD-020)	Fear temperature max. 200 C
GSOT15	SOT-23	15	Standard	8.8 mg	UL 94 V-0	MSL level 1	Peak temperature max. 260 °C
430113	301-23	15G	Green	8.1 mg	OL 94 V-0	(according J-STD-020)	reak temperature max. 200 C
GSOT24	SOT-23	24	Standard	8.8 mg	UL 94 V-0	MSL level 1	Peak temperature max. 260 °C
430124	301-23	24G	Green	8.1 mg	OL 34 V-0	(according J-STD-020)	l ear temperature max. 200 C
GSOT36	SOT-23	36	Standard	8.8 mg	UL 94 V-0	MSL level 1	Peak temperature max. 260 °C
G30130	301-23	36G	Green	8.1 mg	UL 34 V-U	(according J-STD-020)	Fear temperature max. 200 C

Rev. 2.6, 04-Jan-2019 Document Number: 85807



ABSOLUTE MAXIMUM RATINGS GSOT03					
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT	
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	I _{PPM}	30	А	
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	P _{PP}	369	W	
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V	± 30	kV	
ESD Illillidrilly	Air discharge acc. IEC 61000-4-2; 10 pulses	V_{ESD}	30	kV	
Operating temperature	Junction temperature	T _J	-40 to +125	°C	
Storage temperature		T _{STG}	-55 to +150	°C	

ABSOLUTE MAXIMUM RATINGS GSOT04					
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT	
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	I _{PPM}	30	А	
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	P _{PP}	429	W	
CCD improvements.	Contact discharge acc. IEC 61000-4-2; 10 pulses	V	± 30	kV	
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	V_{ESD}	± 30	kV	
Operating temperature	Junction temperature	T _J	-40 to +125	°C	
Storage temperature		T _{STG}	-55 to +150	°C	

ABSOLUTE MAXIMUM RATINGS GSOT05						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	I _{PPM}	30	Α		
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	P _{PP}	480	W		
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V	± 30	kV		
ESD IIIIIIdility	Air discharge acc. IEC 61000-4-2; 10 pulses	V_{ESD}	± 30	kV		
Operating temperature	Junction temperature	T _J	-40 to +125	°C		
Storage temperature		T _{STG}	-55 to +150	°C		

ABSOLUTE MAXIMUM RATINGS GSOT08						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	I _{PPM}	18	А		
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	P_{PP}	345	W		
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V	± 30	kV		
ESD Illillurilly	Air discharge acc. IEC 61000-4-2; 10 pulses	V_{ESD}	± 30	kV		
Operating temperature	Junction temperature	TJ	-40 to +125	°C		
Storage temperature		T _{STG}	-55 to +150	°C		



ABSOLUTE MAXIMUM RATINGS GSOT12						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	I _{PPM}	12	А		
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	P _{PP}	312	W		
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V	± 30	kV		
ESD illillidility	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV		
Operating temperature	Junction temperature	T_J	-40 to +125	°C		
Storage temperature		T _{STG}	-55 to +150	°C		

ABSOLUTE MAXIMUM RATINGS GSOT15						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	I _{PPM}	8	Α		
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	P _{PP}	230	W		
CCD images up its s	Contact discharge acc. IEC 61000-4-2; 10 pulses	V	± 30	kV		
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	V_{ESD}	± 30	kV		
Operating temperature	Junction temperature	T _J	-40 to +125	°C		
Storage temperature		T _{STG}	-55 to +150	°C		

ABSOLUTE MAXIMUM RATINGS GSOT24					
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT	
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	I _{PPM}	5	А	
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	P _{PP}	235	W	
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V	± 30	kV	
ESD IIIIIIdility	Air discharge acc. IEC 61000-4-2; 10 pulses	V_{ESD}	± 30	kV	
Operating temperature	Junction temperature	T _J	-40 to +125	°C	
Storage temperature		T _{STG}	-55 to +150	°C	

ABSOLUTE MAXIMUM RATINGS GSOT36					
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT	
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, t_p = 8/20 μ s; single shot	I _{PPM}	3.5	Α	
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	P _{PP}	248	W	
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V	± 30	kV	
ESD IIIIIIdility	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV	
Operating temperature	Junction temperature	T_J	-40 to +125	°C	
Storage temperature		T _{STG}	-55 to +150	°C	



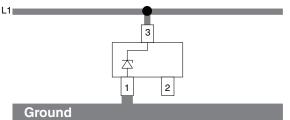
BIAs-MODE (1-line Bidirectional Asymmetrical protection mode)

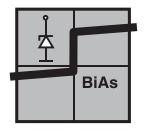
With the GSOTxx one signal- or data-lines (L1) can be protected against voltage transients. With pin 1 connected to ground and pin 3 connected to a signal- or data-line which has to be protected. As long as the voltage level on the data- or signal-line is between 0 V (ground level) and the specified maximum reverse working voltage (V_{RWM}) the protection diode between pin 1 and pin 3 offers a high isolation to the ground line. The protection device behaves like an open switch.

As soon as any positive transient voltage signal exceeds the breakdown voltage level of the protection diode, the diode becomes conductive and shorts the transient current to ground. Now the protection device behaves like a closed switch. The clamping voltage (V_C) is defined by the breakdown voltage (V_{BR}) level plus the voltage drop at the series impedance (resistance and inductance) of the protection diode.

Any negative transient signal will be clamped accordingly. The negative transient current is flowing in the forward direction through the protection diode. The low forward voltage (V_F) clamps the negative transient close to the ground level.

Due to the different clamping levels in forward and reverse direction the GSOTxx clamping behavior is Bidirectional and Asymmetrical (BiAs).





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ELECTRICAL CHARACTERISTICS GSOT03 ($T_{amb} = 25$ °C unless otherwise specified) between pin 3 and pin 1							
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Protection paths	Number of lines which can be protected	N _{channel}	=	-	1	lines	
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	=	-	3.3	V	
Reverse voltage	at I _R = 100 μA	V_R	3.3	-	-	V	
Reverse current	at V _R = 3.3 V	I _R	-	-	100	μΑ	
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	4	4.6	5.5	V	
Deverse elemning veltage	at I _{PP} = 1 A	V	-	5.7	7.5	V	
Reverse clamping voltage	at I _{PP} = I _{PPM} = 30 A	V _C	-	10	12.3	V	
Converd elements veltage	at I _{PP} = 1 A	V	-	1	1.2	V	
Forward clamping voltage	at I _{PP} = I _{PPM} = 30 A	V _F	-	4.5	-	V	
Capacitance	at V _R = 0 V; f = 1 MHz	_	-	420	600	pF	
	at V _R = 1.6 V; f = 1 MHz	C _D	=	260	-	pF	

ELECTRICAL CHARACTERISTICS GSOT04 (T _{amb} = 25 °C unless otherwise specified) between pin 3 and pin 1						
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	-	-	4	V
Reverse voltage	at I _R = 20 μA	V_R	4	-	-	V
Reverse current	at V _R = 4 V	I _R	-	-	20	μΑ
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	5	6.1	7	V
Deverse elemning veltage	at I _{PP} = 1 A	V	-	7.5	9	V
Reverse clamping voltage	at I _{PP} = I _{PPM} = 30 A	V _C	i	11.2	14.3	V
	at I _{PP} = 1 A		-	1	1.2	V
Forward clamping voltage	at I _{PP} = I _{PPM} = 30 A	V _F	-	4.5	-	V
Capacitance	at $V_R = 0 V$; $f = 1 MHz$	_	-	310	450	pF
	at V _R = 2 V; f = 1 MHz	C _D	-	200	-	pF



ELECTRICAL CHARACTERISTICS GSOT05 (T _{amb} = 25 °C unless otherwise specified) between pin 3 and pin 1						
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	=	-	5	V
Reverse voltage	at I _R = 10 μA	V_R	5	-	-	V
Reverse current	at V _R = 5 V	I _R	=	-	10	μΑ
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	6	6.8	8	V
Reverse clamping voltage	at I _{PP} = 1 A	V _C	=	7	8.7	V
	at I _{PP} = I _{PPM} = 30 A		=	12	16	V
Forward clamping voltage	at I _{PP} = 1 A	V _F	-	1	1.2	V
	at I _{PP} = I _{PPM} = 30 A		=	4.5	-	V
Capacitance	at V _R = 0 V; f = 1 MHz	C _D	-	260	350	pF
	at V _R = 2.5 V; f = 1 MHz		-	150	-	pF

ELECTRICAL CHARACTERISTICS GSOT08 (T _{amb} = 25 °C unless otherwise specified) between pin 3 and pin 1						
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	=	-	1	lines
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	-	-	8	V
Reverse voltage	at I _R = 5 μA	V_R	8	-	-	V
Reverse current	at $V_R = 8 V$	I _R	-	-	5	μΑ
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	9	10	11	V
Payaraa alamping valtaga	at I _{PP} = 1 A	- V _C	-	10.7	13	V
Reverse clamping voltage	at I _{PP} = I _{PPM} = 18 A		-	15.2	19.2	V
Forward alamping voltage	at I _{PP} = 1 A	V _F	-	1	1.2	V
Forward clamping voltage	at I _{PP} = I _{PPM} = 18 A		-	3	-	V
Capacitance	at V _R = 0 V; f = 1 MHz	- C _D	-	160	250	pF
	at V _R = 4 V; f = 1 MHz		-	80	-	pF

ELECTRICAL CHARACTERISTICS GSOT12 (T _{amb} = 25 °C unless otherwise specified) between pin 3 and pin 1							
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Protection paths	Number of lines which can be protected	N _{channel}	=	-	1	lines	
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	=	-	12	V	
Reverse voltage	at I _R = 1 μA	V_R	12	-	-	V	
Reverse current	at V _R = 12 V	I _R	-	-	1	μΑ	
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	13.5	15	16.5	V	
	at I _{PP} = 1 A	V _C	-	15.4	18.7	V	
Reverse clamping voltage	at I _{PP} = I _{PPM} = 12 A		-	21.2	26	V	
Forward clamping voltage	at I _{PP} = 1 A	.,	-	1	1.2	V	
	at I _{PP} = I _{PPM} = 12 A	V _F	-	2.2	-	V	
Capacitance	at V _R = 0 V; f = 1 MHz	- C _D	-	115	150	pF	
	at V _R = 6 V; f = 1 MHz		-	50	-	pF	



ELECTRICAL CHARACTERISTICS GSOT15 (T _{amb} = 25 °C unless otherwise specified) between pin 3 and pin 1							
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Protection paths	Number of lines which can be protected	N _{channel}	=	-	1	lines	
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	=	-	15	V	
Reverse voltage	at I _R = 1 μA	V_R	15	-	-	V	
Reverse current	at V _R = 15 V	I _R	-	-	1	μA	
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	16.5	18	20	V	
	at I _{PP} = 1 A	V _C	=	19.4	23.5	V	
Reverse clamping voltage	at I _{PP} = I _{PPM} = 8 A		-	24.8	28.8	V	
Forward clamping voltage	at I _{PP} = 1 A	V _F	-	1	1.2	V	
	at I _{PP} = I _{PPM} = 8 A		-	1.8	=	V	
Capacitance	at V _R = 0 V; f = 1 MHz	- C _D	-	90	120	pF	
	at V _R = 7.5 V; f = 1 MHz		=	35	-	pF	

ELECTRICAL CHARACTERISTICS GSOT24 (T _{amb} = 25 °C unless otherwise specified) between pin 3 and pin 1						
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	-	-	24	V
Reverse voltage	at I _R = 1 μA	V_R	24	-	-	V
Reverse current	at V _R = 24 V	I _R	-	-	1	μΑ
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	27	30	33	V
Deverse elemning veltage	at I _{PP} = 1 A	V _C	-	34	41	V
Reverse clamping voltage	at I _{PP} = I _{PPM} = 5 A		-	41	47	V
Forward clamping voltage	at I _{PP} = 1 A		-	1	1.2	V
	at I _{PP} = I _{PPM} = 5 A	V _F	-	1.4	-	V
Capacitance	at V _R = 0 V; f = 1 MHz	- C _D	-	65	80	pF
	at V _R = 12 V; f = 1 MHz		-	20	=	pF

ELECTRICAL CHARACTERISTICS GSOT36 (T _{amb} = 25 °C unless otherwise specified) between pin 3 and pin 1						
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	=	-	1	lines
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	=	-	36	V
Reverse voltage	at I _R = 1 μA	V_R	36	-	-	V
Reverse current	at V _R = 36 V	I _R	-	-	1	μΑ
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	39	43	47	V
Deverse elemning voltage	at I _{PP} = 1 A	- V _C	-	49	60	V
Reverse clamping voltage	at I _{PP} = I _{PPM} = 3.5 A		-	59	71	V
Forward clamping voltage	at I _{PP} = 1 A	V _F	-	1	1.2	V
	at I _{PP} = I _{PPM} = 3.5 A		-	1.3	-	V
Capacitance	at V _R = 0 V; f = 1 MHz	- C _D	-	52	65	pF
	at V _R = 18 V; f = 1 MHz		-	12	-	pF



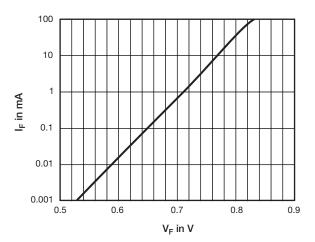


Fig. 1 - Typical Forward Current I_F vs. Forward Voltage V_F

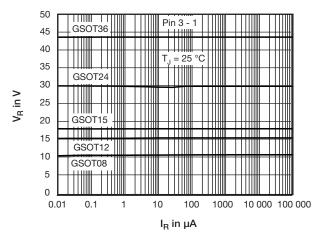


Fig. 2 - Typical Reverse Voltage V_{R} vs. Reverse Current I_{R}

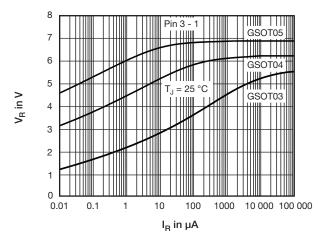
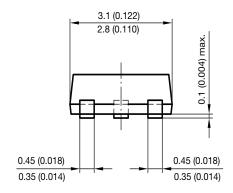
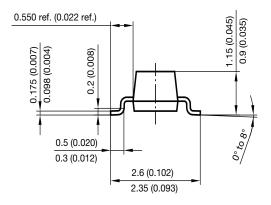


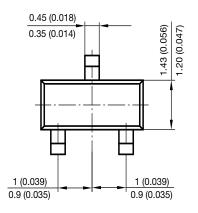
Fig. 3 - Typical Reverse Voltage V_{R} vs. Reverse Current I_{R}

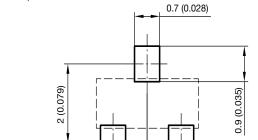
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PACKAGE DIMENSIONS in millimeters (inches): SOT-23





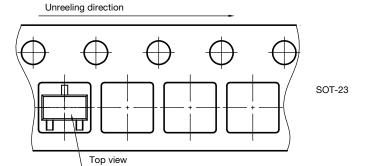




Foot print recommendation:

Document no.: 6.541-5014.01-4 Rev. 8 - Date: 23. Sep. 2009

17418



0.95 (0.037)

Orientation in carrier tape SOT-23 S8-V-3929.01-006 (4) 04.02.2010 22607



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Vishay

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